SAMPLING POSITIONING METHOD OF STROBOSCOPIC ELECTRON BEAM APPARATUS

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Applicant:

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- european:

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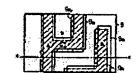
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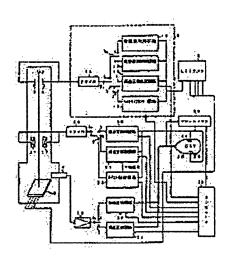
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Abstract of JP2080970

PURPOSE:To enhance voltage measuring accuracy by eliminating that the edge of an electrode to be measured or a region other than the electrode to be measured is irradiated with primary beam by setting a region, where secondary electron images mutually overlap at all of the measuring positions of the voltage waveform of a stroboscopic electron beam apparatus capable of measuring a voltage waveform with high accuracy, to a voltage waveform measuring position.

CONSTITUTION:A sample 5 is operated by an LSI tester and primary beam is deflected by a high speed phase scanning circuit 18 or a multi-sampling circuit 19 and an image becomes a potential contrast image 9 wherein potential contrast images in all of the phases of a measured voltage waveform overlap mutually. Next, the image 9 is taken in a frame memory 28 and a waveform observing mode is set in such a state that the image 9 is displayed on the picture of a CRT 25 to set a sampling position in a region where the patterns 9a, 9b of the region of an electrode to be measured in the image 9 overlap mutually by a point control circuit 22.





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